

U.S. Application No. 10/051,267

Attorney Docket No. 09792909-5359

REMARKS

Claims 1-3 are presently pending in the application. Claims 4-9, 11 and 13 have been canceled without prejudice or disclaimer, and Claims 10 and 12 have been withdrawn as being drawn to a non-elected species. Reconsideration and allowance of all claims are respectfully requested in view of the following remarks.

Enclosed is a Credit Card Payment Form authorizing payment of the fees for a three month extension of time.

As a preliminary matter, the Examiner is respectfully requested to acknowledge receipt of three (3) sheets of Proposed Drawing Corrections, which corrects FIG. 2D to FIG. 2E, which changes the numbering of FIGS. 3G-3J to 3A-3D, and which adds reference numeral 201 to FIG. 6. Once approved, corrected formal drawings will follow.

The Examiner has acknowledged the claim for foreign priority, but alleges that the certified copy of the foreign application still has to be filed.

The Applicants respectfully point out to the Examiner that the certified copy of the foreign application was filed in the parent case U.S. Patent Application No. 09/827,676, and thus, no certified copy need be filed in the divisional application.

The Examiner has rejected Claims 1 and 2 under 35 U.S.C. §102(e) as being anticipated by Kawasaki et al. (U.S. Patent No. 6,281,552). Further, the Examiner has rejected Claim 3 under 35 U.S.C. §103(a) as being unpatentable over Kawasaki et al. (U.S. Patent No. 6,281,552) in view of Yamazaki et al. (U.S. Patent No. 6,246,070). Claim 1 has been amended for purposes of form only, and are not related to patentability. For the following reasons, the prior art rejections are respectfully traversed.

The Applicants respectfully submit that Kawasaki et al. do not teach or suggest a bottom gate thin film transistor wherein there is no etched mask structure within the thin film transistor structure, as recited in Claim 1.

Rather, Kawasaki et al. disclose doping with an impurity element by first forming a resist mask and etching unnecessary portions to form spacer films 107, 109 (see col. 6, lines 24-40). Further, doping with an impurity element for imparting P type to form a source region and drain region in the P channel type TFT, a new resist mask 126 is formed, and etching treatment is performed on the first and second spacer films to form

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new spacer films 129, 130, to expose the surface of the crystalline silicon film before the impurity regions are formed (see col. 7, lines 9-20).

Accordingly, Claim 1 is not anticipated nor obvious over Kawasaki et al., and the rejection of Claim 1 under 35 U.S.C. §102(e) should be withdrawn.

Further, since Claim 2 depends from Claim 1, it is also patentably distinguishable over Kawasaki et al. for the reasons cited above with respect to Claim 1.

The addition of the Yamazaki et al. reference does not make up for the deficiencies in Kawasaki et al. Thus, Claim 3 is patentable over either the individual or the combination of the Kawasaki et al. and Yamazaki et al. references for the reasons cited above with respect to Claim 1.

If the Examiner believes that there is any issue which could be resolved by a telephone or personal interview, the Examiner is respectfully requested to contact the undersigned attorney at the telephone number listed below.

Respectfully submitted,



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